## NSN 5961-01-322-4576

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View Online at https://aerobasegroup.com/nsn/5961-01-322-4576

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Inclosure Material:
Metal
Overall Length:
1.573 inches
Overall Height:
0.350 inches
Overall Width:
1.050 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-3
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Features Provided:
Quality assurance level txv and burn in and hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
850.0 collector-to-emitter substaining voltage, with specified circuit between base and emitter and 400.0 collector to emitter
voltage/static/base open and 9.0 emitter to base voltage, static, collector open
Current Rating Per Characteristic:
Between 10.00 amperes source cutoff current and 15.00 amperes source cutoff current
Power Rating Per Characteristic:
175.0 watts small-signal input power, common-collector preset
Transfer Ratio:
6.0 static forward current transfer ratio, common-emitter
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Junction pattern arrangement: npn
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
1 case and 2 pin
Specification Data:

NI/o

Shelf Life:

81349-mil-s-19500/525 government specification

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Demilitarization:

No

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